# **General Purpose Transistors**

#### **PNP Silicon**

#### **Feature**

• Pb–Free Package May be Available. The G–Suffix Denotes a Pb–Free Lead Finish

#### **MAXIMUM RATINGS**

Rating	Symbol	2907A	Unit
Collector-Emitter Voltage	$V_{CEO}$	-60	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-60	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	-600	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



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http://onsemi.com

# COLLECTOR 3 BASE 2

**EMITTER** 



SOT-23 (TO-236AB) CASE 318 STYLE 6

#### **DEVICE MARKING**



x = Monthly Date Code

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MMBT2907ALT1	SOT-23	3000 Units/Reel	
MMBT2907ALT3G	SOT-23	3000 Units/Reel	

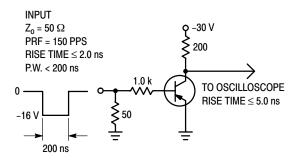
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Charac	teristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				I	
Collector-Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)		V <sub>(BR)CEO</sub>	-60	-	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = –10 μAdc, I <sub>E</sub> = 0)		V <sub>(BR)CBO</sub>	-60	_	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = -10 µAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = -30 Vdc, V <sub>BE(off)</sub> = -0.5 Vdc)		I <sub>CEX</sub>	_	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$		I <sub>CBO</sub>	- -	-0.010 -10	μAdc
Base Current (V <sub>CE</sub> = -30 Vdc, V <sub>EB(off)</sub> = -0.5 Vdc)		I <sub>B</sub>	-	-50	nAdc
ON CHARACTERISTICS		•	•	•	•
$\label{eq:continuous} \begin{array}{l} \text{DC Current Gain} \\ \text{($I_{C} = -0.1$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -1.0$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -10$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -150$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = -500$ mAdc, $V_{CE} = -10$ Vdc)} \\ \text{($I_{C} = $		h <sub>FE</sub>	75 100 100 100 50	- - 300 -	_
Collector-Emitter Saturation Voltage (Note 3) ( $I_C = -150$ mAdc, $I_B = -15$ mAdc) (Note 3) ( $I_C = -500$ mAdc, $I_B = -50$ mAdc)		V <sub>CE(sat)</sub>	- -	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)		V <sub>BE(sat)</sub>	-	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS		•	•	•	
Current – Gain – Bandwidth Product (Notes 3, 4) (I <sub>C</sub> = –50 mAdc, V <sub>CE</sub> = –20 Vdc, f = 100 MHz	•	f <sub>T</sub>	200	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	-	8.0	pF
Input Capacitance (V <sub>EB</sub> = -2.0 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>	-	30	-
SWITCHING CHARACTERISTICS					
Turn-On Time		t <sub>on</sub>	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t <sub>d</sub>	-	10	
Rise Time	<u> </u>	t <sub>r</sub>	-	40	
Turn-Off Time		t <sub>off</sub>	_	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	ts	_	80	
Fall Time	,	t <sub>f</sub>	-	30	

- 3. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%. 4. f<sub>T</sub> is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.





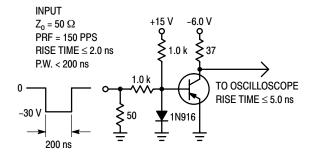


Figure 2. Storage and Fall Time Test Circuit

#### **TYPICAL CHARACTERISTICS**

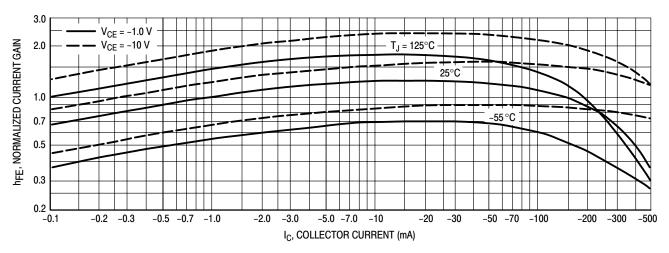


Figure 3. DC Current Gain

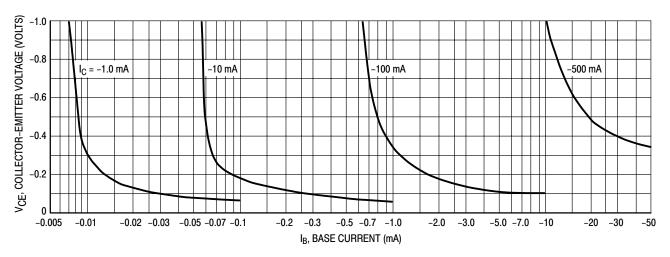


Figure 4. Collector Saturation Region

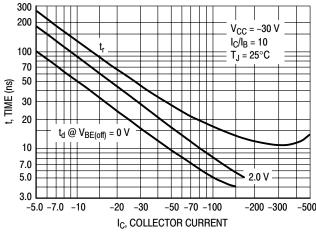


Figure 5. Turn-On Time

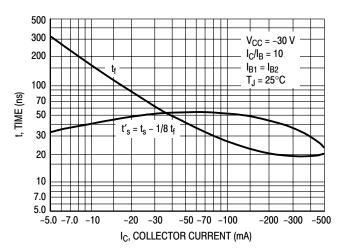
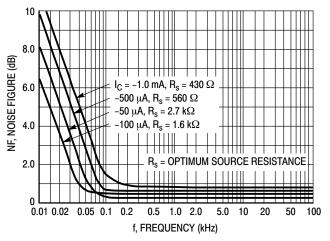


Figure 6. Turn-Off Time

## TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

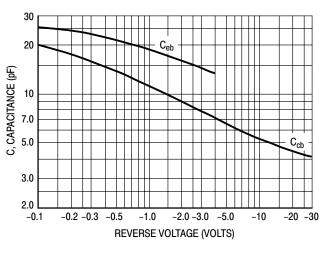
 $V_{CE} = 10 \text{ Vdc}, T_A = 25^{\circ}\text{C}$ 



8.0 NF, NOISE FIGURE (dB) 6.0  $I_C = -50 \mu A$ -100 μA -500 μ**A** 4.0 -1.0 mA 2.0 100 200 2.0 k 20 k 50 k 50 1.0 k 5.0 k 10 k Rs, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



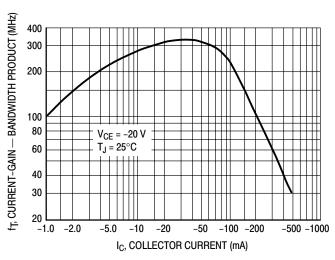
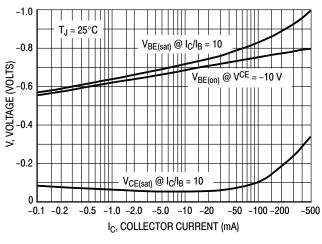


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



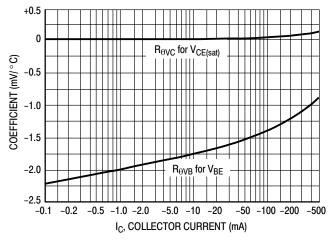
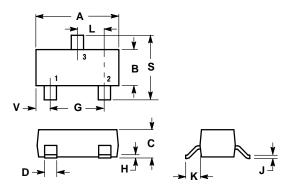


Figure 11. "On" Voltage

**Figure 12. Temperature Coefficients** 

#### PACKAGE DIMENSIONS

SOT-23 (TO-236AB) CASE 318-08 **ISSUE AH** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
٧	0.0177	0.0236	0.45	0.60

STYLE 6:

BASE PIN 1.

- EMITTER
- 3 COLLECTOR

#### **SOLDERING FOOTPRINT\***

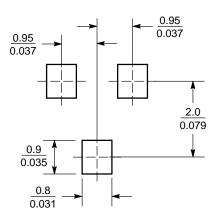


Figure 13. SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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